

PROCEEDINGS OF SPIE

Metrology, Inspection, and Process Control XXXVII

John C. Robinson
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Editors

27 February – 2 March 2023
San Jose, California, United States

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Published by
SPIE

Volume 12496

Part One of Two Parts

Proceedings of SPIE 0277-786X, V. 12496

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

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Please use the following format to cite material from these proceedings:

Author(s), "Title of Paper," in *Metrology, Inspection, and Process Control XXXVII*, edited by John C. Robinson, Matthew J. Sendelbach, Proc. of SPIE 12496, Seven-digit Article CID Number (DD/MM/YYYY); (DOI URL).

ISSN: 0277-786X

ISSN: 1996-756X (electronic)

ISBN: 9781510660991

ISBN: 9781510661004 (electronic)

Published by

SPIE

P.O. Box 10, Bellingham, Washington 98227-0010 USA

Telephone +1 360 676 3290 (Pacific Time)

SPIE.org

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